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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

WASHINGTON, D.C. 20231

Inventor: **Zhang et al.**

Serial No: **09/357264**

Filed: **July 19, 1999**

For: **Comp. for Chemical Mechanical  
Planarization of Copper,  
Tantalum and Tantalum Nitride**

Examiner: Brown, Charlotte A.

Art Unit: 1765

**RECEIVED**

JUN 05 2002

**TC 1700**

**RESPONSE TO OFFICE ACTION**

The Honorable Commissioner  
of Patents and Trademarks  
Washington, D.C. 20231

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ORIGINALLY FILED

Dear Sir:

This paper responds to the Office Action dated February 20, 2002. Please enter the following (**Clean Copy** of Amended Claims follows with non-amended claims in italics for your immediate reference. A **Marked Up Copy** of the Amended Claims and a **full Clean Copy** of the Claims to be entered are attached hereto):

**IN THE CLAIMS**

1. *A chemical mechanical planarization system that includes a Cu/Ta/TaN surface, a single-slurry solution comprising:*
  - a) *an oxidizing reactant selected from the group consisting of H<sub>2</sub>O<sub>2</sub>, HNO<sub>3</sub> and mixtures thereof; and*
  - b) *a co-reactant is selected from the group consisting of H<sub>3</sub>PO<sub>4</sub>, H<sub>2</sub>SO<sub>4</sub>, HNO<sub>3</sub>, oxalic acid, acetic acid, organic acids and mixtures thereof.*